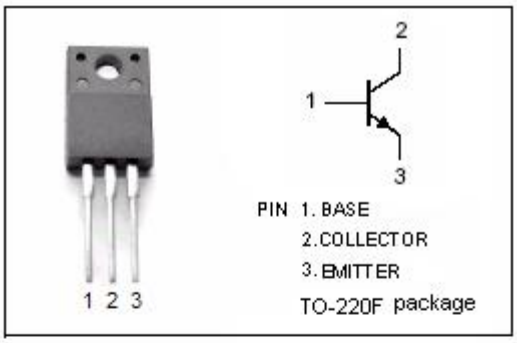
isc Silicon NPN Power Transistor — 2SC5895

DESCRIPTION

- High Breakdown Voltage
- Wide Area of Safe Operation
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

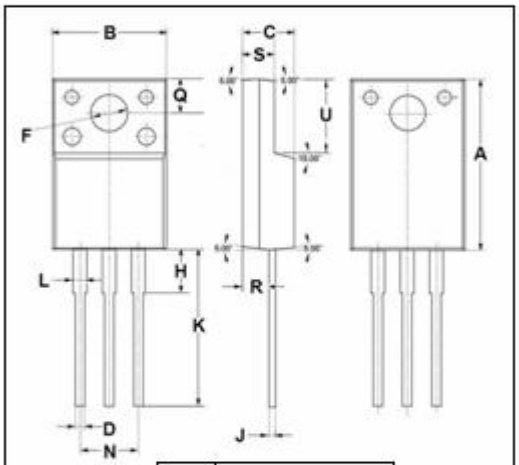


APPLICATIONS

- Power supply for audio & visual equipments such as TVS and VCRS
- Industrial equipments such as DC-DC converters

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	60	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current- Continuous	2	A
I_B	Base Current- Continuous	0.5	A
I_{CP}	Collector Current-Pulse	4	A
P_C	Collector Power Dissipation @ T_a=25℃	2	W
	Collector Power Dissipation @ T_C=25℃	15	
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



DIM	mm MIN	MAX
A	14.95	15.05
B	10.00	10.10
C	4.40	4.60
D	0.75	0.90
F	3.10	3.30
H	3.70	3.90
J	0.50	0.70
K	13.4	13.6
L	1.10	1.30
N	5.00	5.20
Q	2.70	2.90
R	2.20	2.40
S	2.65	2.90
U	6.40	6.60

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 2A; I_B= 0.25A			0.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 60V; I_E= 0			100	μA
h_{FE-1}	DC Current Gain	I_C= 1A; V_{CE}= 4V	80		250	
h_{FE-2}	DC Current Gain	I_C= 0.2A; V_{CE}= 4V	60			
h_{FE-3}	DC Current Gain	I_C= 2A; V_{CE}= 4V	30			
t_{stg}	Storage Time	I_C= 1A, I_{B1}= 0.1A; I_{B2}= -0.1A		0.7		μs
t_f	Fall Time			0.15		μs